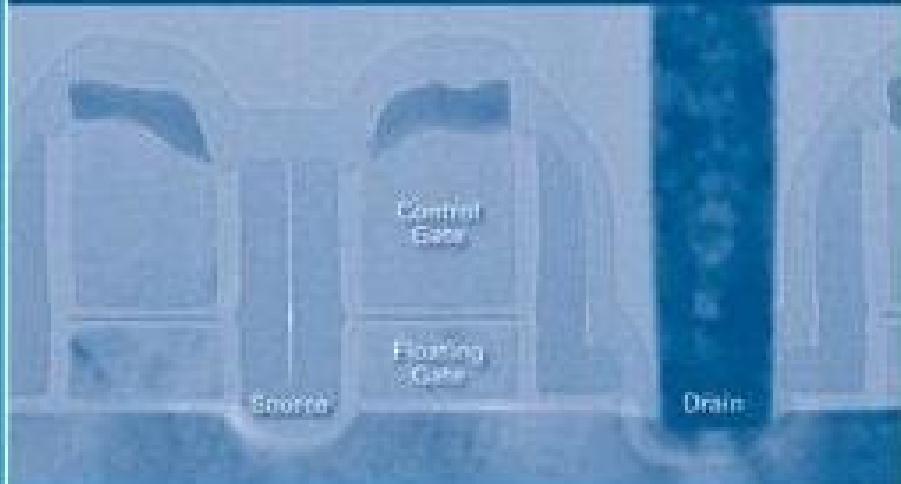


IEEE Press Series on Microelectronic Systems
Stuart K. Tewksbury and Joe E. Brewer, Series Editors

Nonvolatile Memory Technologies *with Emphasis on Flash*



*A Comprehensive Guide to
Understanding and Using NVM Devices*

Edited by
JOE E. BREWER and MANZUR GILL

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